

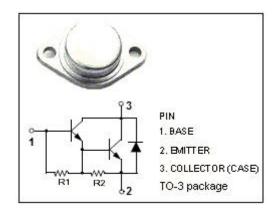
isc Silicon NPN Darlingtion Power Transistor

DESCRIPTION

- · Built-in Base-Emitter Shunt Resistors
- High DC current gainh_{FE} = 1000 (Min) @ I_C = 5A
- Collector-Emitter Breakdown Voltage-V(BR)CEO= 80V(Min)
- Complement to PNP type MJ2501
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



 Designed for use as output devices in complementary general purpose amplifier applications.

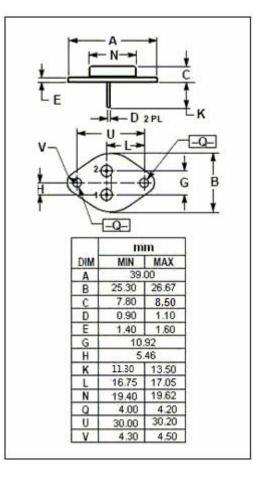


ABSOLUTE MAXIMUM RATINGS(T_c=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|-------------------------------------------------|-------|------------|--|
| V _{CBO} | Collector-Base Voltage | 80 | V | |
| V _{CEO} | Collector-Emitter Voltage | 80 | V | |
| V _{EBO} | Emitter-Base Voltage | 5 | V | |
| Ic | Collector Current -Continuous | 10 | Α | |
| lΒ | Base Current | 0.2 | Α | |
| Pc | Collector Power Dissipation@T _C =25℃ | 150 | W | |
| TJ | Junction Temperature | 200 | $^{\circ}$ | |
| T _{stg} | Storage Temperature -55~20 | | $^{\circ}$ | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|--------------------------------------|------|------|
| R _{th j-c} | Thermal Resistance, Junction to Case | 1.17 | °C/W |





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MJ3001

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|------------------------|--------------------------------------|-----------------------------------------------------------------|------|-----|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 50mA; I _B = 0 | 80 | | V |
| V _{CE(sat)-1} | Collector-Emitter Saturation Voltage | I _C = 5A; I _B = 20mA | | 2.0 | V |
| V _{CE(sat)-2} | Collector-Emitter Saturation Voltage | I _C = 10A; I _B = 50mA | | 4.0 | V |
| V _{BE(on)} | Base-Emitter On voltage | I _C = 5A; V _{CE} = 3V | | 3.0 | V |
| I _{CEO} | Collector Cutoff current | V _{CE} = 40V; I _B = 0 | | 1.0 | mA |
| Ісво | Collector Cutoff current | V _{CB} = 80V; I _E = 0,T _C =150°C | | 1.0 | mA |
| I _{EBO} | Emitter Cut-off current | V _{EB} = 5V; I _C = 0 | | 2.0 | mA |
| h _{FE} | DC Current Gain | I _C = 5A; V _{CE} = 3V | 1000 | | |

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